

TRANSPARENT AMORPHOUS CARBON STRUCTURE IN SEMICONDUCTOR DEVICES

Abstract

5 A transparent amorphous carbon layer is formed. The transparent
amorphous carbon layer has a low absorption coefficient such that the amorphous
carbon is transparent in visible light. The transparent amorphous carbon layer may
be used in semiconductor devices for different purposes. The transparent
amorphous carbon layer may be included in a final structure in semiconductor
10 devices. The transparent amorphous carbon layer may also be used as a mask in an
etching process during fabrication of semiconductor devices.

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